

OQ 15104102

ABSTRACT OF THE DISCLOSURE

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A light-emitting layer is provided on a substrate. A p-type semiconductor layer is provided on the light-emitting layer. An upper electrode is provided on the p-type semiconductor layer. The upper electrode includes an Au thin film coming into contact with the p-type semiconductor layer and an n-type transparent conductor film formed thereon. The n-type transparent conductor film is formed by laser ablation.